

4V Drive Pch MOSFET

RW1E025RP

● Structure

Silicon P-channel MOSFET

● Features

- 1) Low On-resistance.
- 2) Small high power package.
- 3) Low voltage drive.(4V)

● Application

Switching

● Packaging specifications

Type	Package	Taping
	Code	T2CR
	Basic ordering unit (pieces)	8000
RW1E025RP		○

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DSS}	-30	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current	Continuous	I_D	± 2.5 A
	Pulsed	I_{DP} *1	± 10 A
Source current (Body Diode)	Continuous	I_S	-0.5 A
	Pulsed	I_{SP} *1	-10 A
Power dissipation	P_D *2	0.7	W
Channel temperature	Tch	150	°C
Range of storage temperature	Tstg	-55 to +150	°C

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

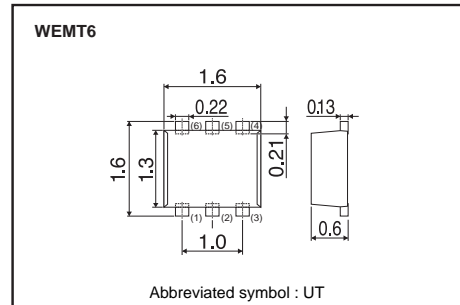
*2 Mounted on a ceramic board.

● Thermal resistance

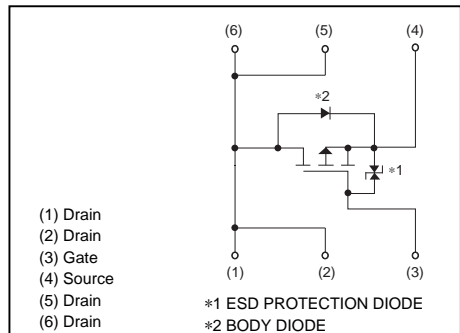
Parameter	Symbol	Limits	Unit
Channel to Ambient	$R_{th}(ch-a)^*$	179	°C / W

*Mounted on a ceramic board.

● Dimensions (Unit : mm)



● Inner circuit



● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$I_D=-1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	-	-	-1	μA	$V_{DS}=-30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	-1.0	-	-2.5	V	$V_{DS}=-10V, I_D=-1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	55	75	m Ω	$I_D=-2.5A, V_{GS}=-10V$
		-	85	115		$I_D=-1.2A, V_{GS}=-4.5V$
		-	95	125		$I_D=-1.2A, V_{GS}=-4V$
Forward transfer admittance	$ Y_{fs} ^*$	1.5	-	-	S	$I_D=-2.5A, V_{DS}=-10V$
Input capacitance	C_{iss}	-	480	-	pF	$V_{DS}=-10V$
Output capacitance	C_{oss}	-	70	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	-	70	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	7	-	ns	$I_D=-1.2A, V_{DD}=-15V$
Rise time	t_r^*	-	12	-	ns	$V_{GS}=-10V$
Turn-off delay time	$t_{d(off)}^*$	-	50	-	ns	$R_L=12.5\Omega$
Fall time	t_f^*	-	22	-	ns	$R_G=10\Omega$
Total gate charge	Q_g^*	-	5.2	-	nC	$I_D=-2.5A$
Gate-source charge	Q_{gs}^*	-	1.6	-	nC	$V_{DD}=-15V$
Gate-drain charge	Q_{gd}^*	-	1.6	-	nC	$V_{GS}=-5V$

*Pulsed

● Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	-1.2	V	$I_S=-2.5A, V_{GS}=0V$

*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics (I)

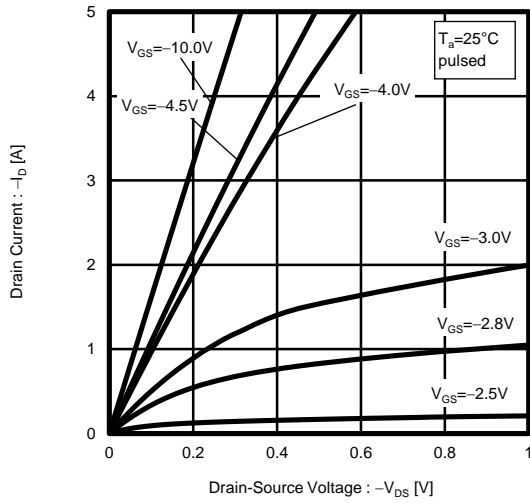


Fig.2 Typical Output Characteristics (II)

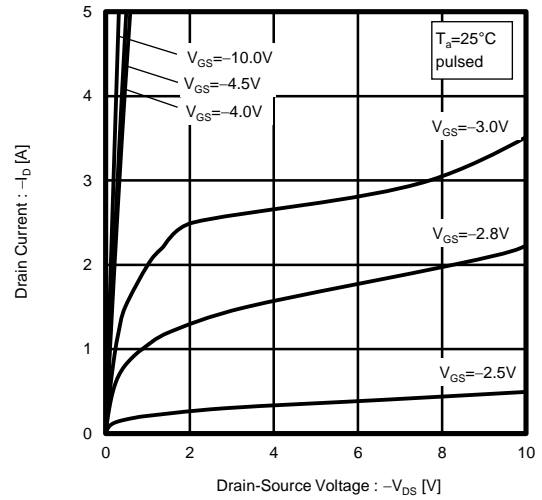


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

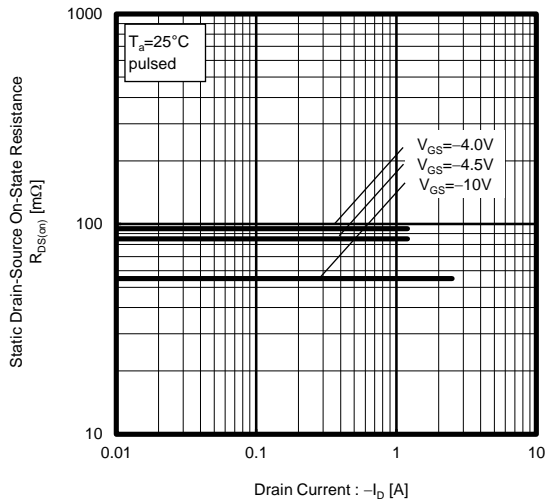


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

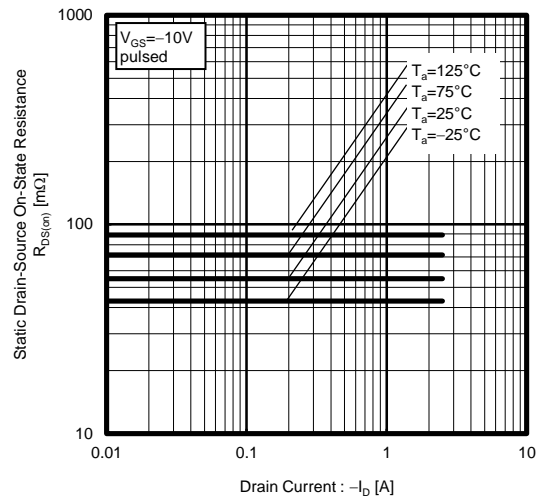


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

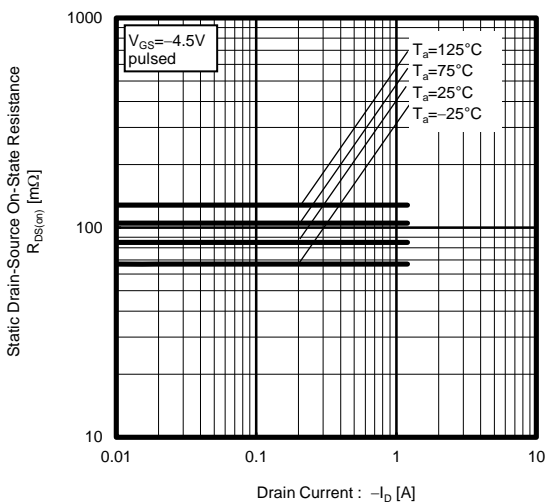


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

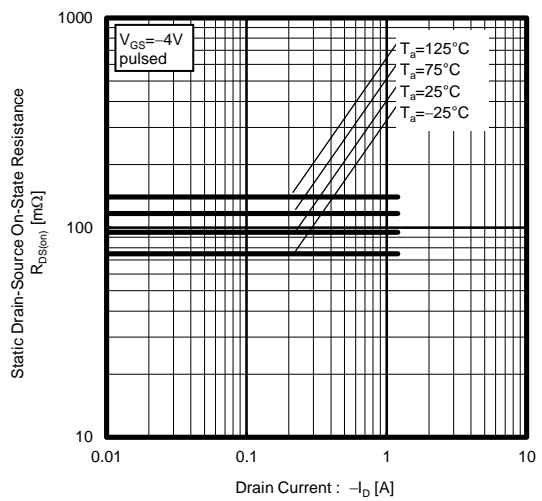


Fig.7 Forward Transfer Admittance vs. Drain Current

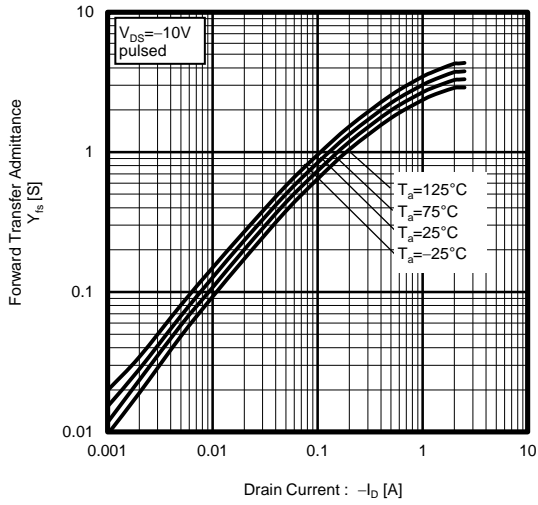


Fig.8 Typical Transfer Characteristics

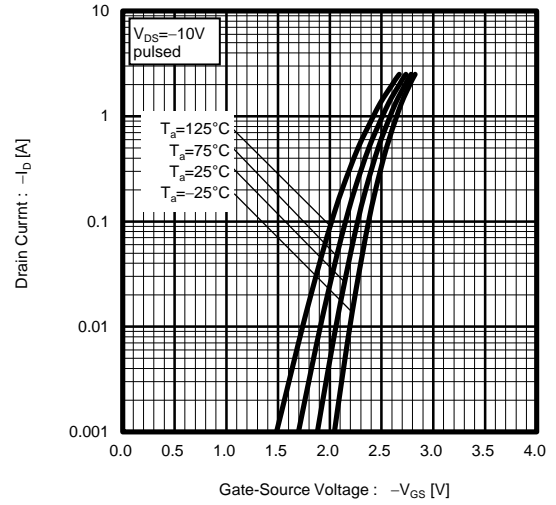


Fig.9 Source Current vs. Source-Drain Voltage

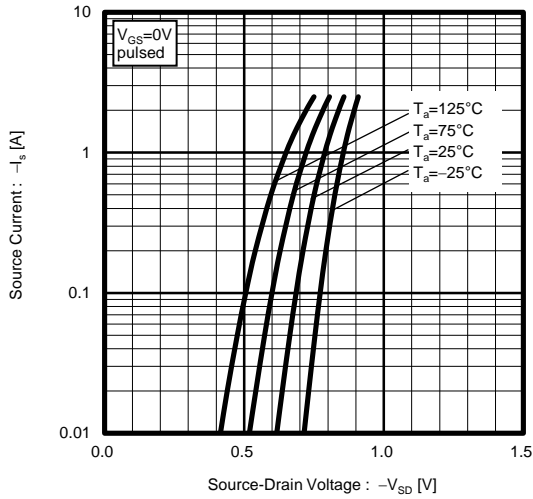


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

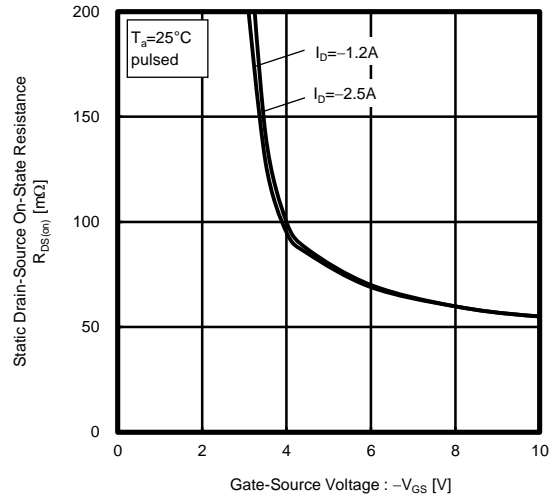


Fig.11 Switching Characteristics

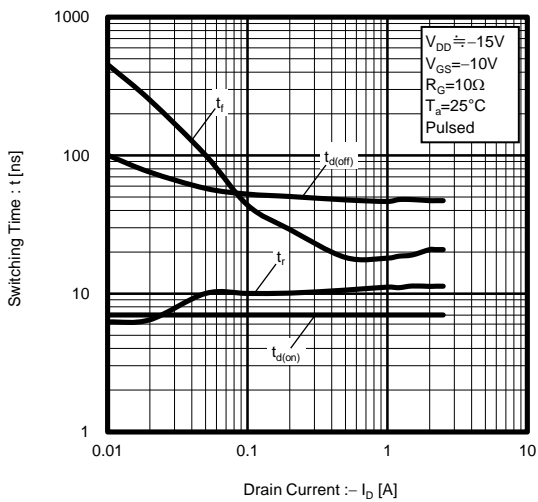


Fig.12 Dynamic Input Characteristics

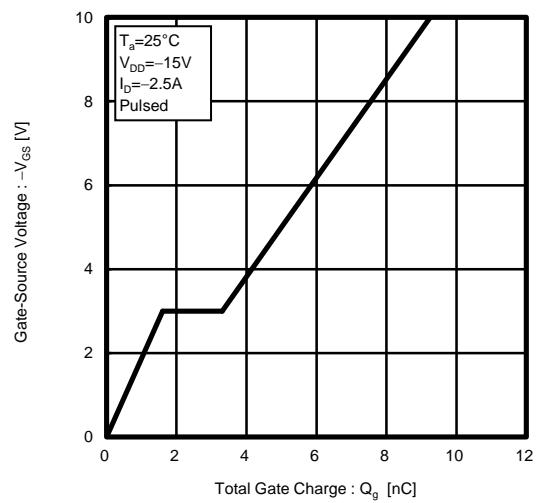
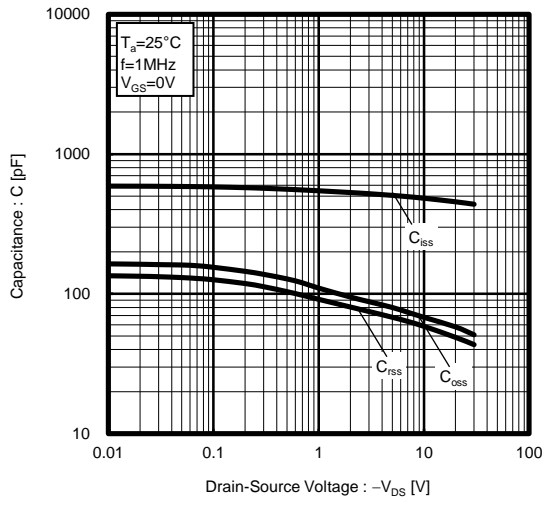


Fig.13 Typical Capacitance vs. Drain-Source Voltage



● Measurement circuits

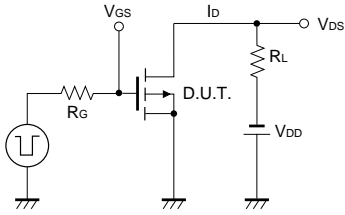


Fig.1-1 Switching Time Measurement Circuit

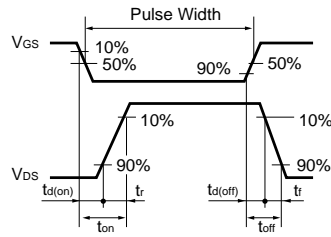


Fig.1-2 Switching Waveforms

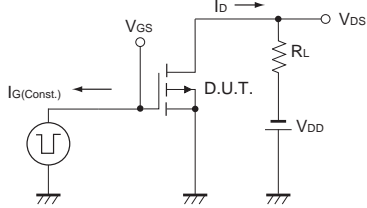


Fig.2-1 Gate Charge Measurement Circuit

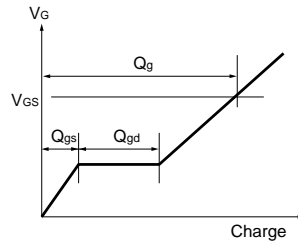


Fig.2-2 Gate Charge Waveform

● Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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